

20V Dual N-Channel MOSFET w/ESD Protected



SOP-8

5

Pin Definition:

1. Source 1	8. Drain 1
2. Gate 1	7. Drain 1
3. Source 2	6. Drain 2
4. Gate 2	5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
20	22 @ V _{GS} = 4.5V	6.5
	29 @ V _{GS} = 2.5V	5.5

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance
- ESD Protect 2KV

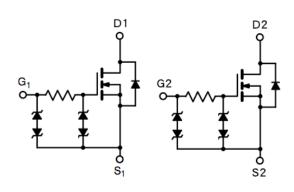
Application

- Specially Designed for Li-on Battery Packs
- Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM7311DCS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	6.5	Α	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	30	Α	
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	1.4	Α	
Maximum Power Dissipation	Ta = 25°C	В	8.5	W	
	Ta = 75°C	P _D	6.4		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	R⊖ _{JF}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	62.5	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.





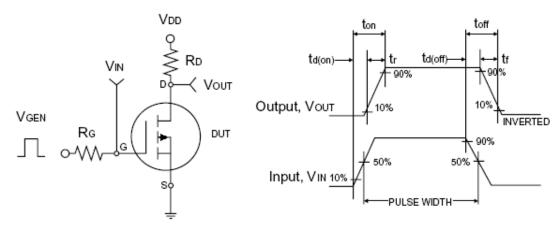
20V Dual N-Channel MOSFET w/ESD Protected

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6	8.0	1.0	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}	1		±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I _{DSS}	1		1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30			Α
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 6.5A$			15	22	mΩ
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 5.5A$	R _{DS(ON)}	1	20	29	
Forward Transconductance	$V_{DS} = 10V, I_D = 6.5A$	g _{fs}	1	30		S
Diode Forward Voltage	$I_S = 1.7A$, $V_{GS} = 0V$	V_{SD}	1	0.6	1.2	V
Dynamic ^b						
Total Gate Charge)/ - 40\/ I - 0.54	Q_g		15	20	
Gate-Source Charge	$V_{DS} = 10V, I_D = 6.5A,$ $V_{GS} = 4.5V$	Q_{gs}		3.4		nC
Gate-Drain Charge	V _{GS} = 4.5 V	Q_{gd}		1.2		
Input Capacitance	\	C _{iss}	-	950		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}	1	450		pF
Reverse Transfer Capacitance	1 - 1.0IVINZ	C _{rss}	1	135		
Switching ^c						
Turn-On Delay Time	V -40V D -400	t _{d(on)}	1	140	200	
Turn-On Rise Time	$V_{DD} = 10V, R_{L} = 10Ω,$ $I_{D} = 1A, V_{GEN} = 4.5V,$ $R_{G} = 6Ω$	t _r	-	210	250	nS
Turn-Off Delay Time		$t_{d(off)}$	-	3700	4800	113
Turn-Off Fall Time	17G - 022	t _f		2000	2600	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

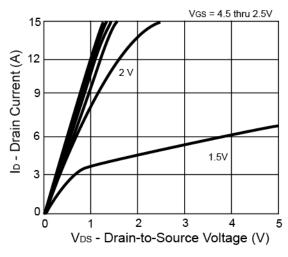




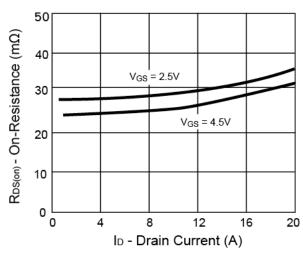


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

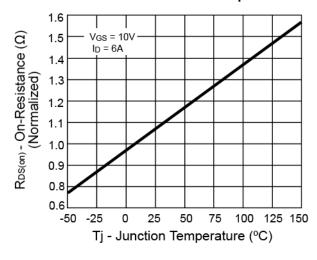




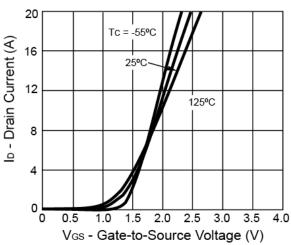
On-Resistance vs. Drain Current



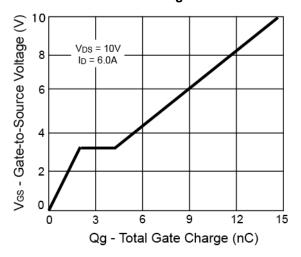
On-Resistance vs. Junction Temperature



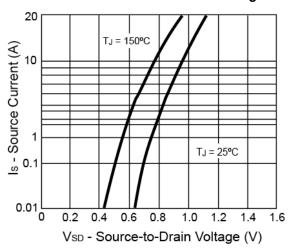
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



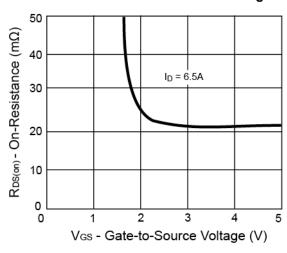


20V Dual N-Channel MOSFET w/ESD Protected

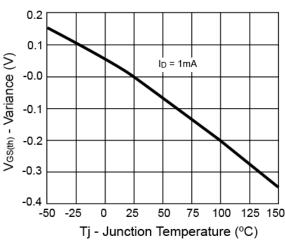


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

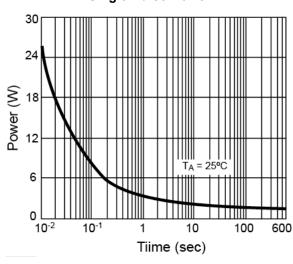
On-Resistance vs. Gate-Source Voltage



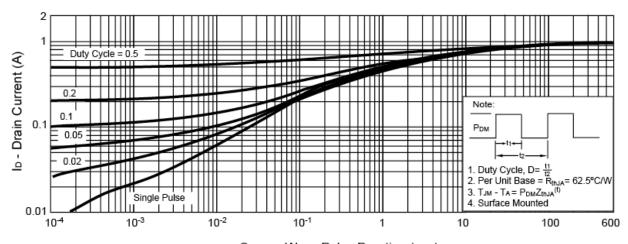
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



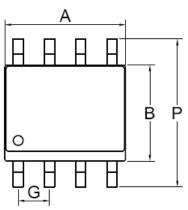
Square Wave Pulse Duration (sec)

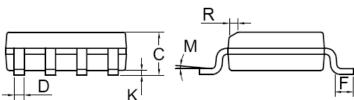




20V Dual N-Channel MOSFET w/ESD Protected

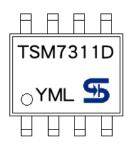
SOP-8 Mechanical Drawing





SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



20V Dual N-Channel MOSFET w/ESD Protected

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.